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INFORMATION DISCLOSURE CITATION

Atty. Docket No.	Appln. No. 10/628,513
Applicant Tsutomu TEZUKA, et al.	
Filing Date July 29, 2003	Group: 2812

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

VAMI	T. Tezuka et al., "Dislocation-free formation of relaxed SiGe-on-insulator layers", American Institute of Physics, Applied Physics Letters, Vol. 80, No. 19, May 13, 2002, pp. 3560-3562

Examiner Victor A. Mandalay	Date Considered 5-24-05
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INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.3105	Application No.	
Applicant	Tsutomu TEZUKA et al.		
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

VAMS	T. Tezuka et al., "Dislocation-free formation of relaxed SiGe-on-insulator layers", American Institute of Physics, (May 13, 2002)
↓	T. Tezuka et al., "Integrated Circuit Device", Application No.: 10/188,824, filed July 5, 2002.
↓	A. Nishida et al., "Elimination of misfit dislocations in Si _{1-x} Ge _x /Si heterostructures by limited-area molecular-beam epitaxial growth", J. Appl. Phys. vol.71 (12), June 15, 1992.

Examiner	<i>Victor A. Mondrago</i>	Date Considered	5-24-05
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Applicant	Tsutomu TEZUKA et al.		
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FOREIGN PATENT DOCUMENTS							
		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
VAMS	T. Mizuno et al., "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology", IEDM Technical Digest, pp. 934-936 (1999).
↓	T. Tezuka et al., "Fabrication of strained Si on an ultrathin SiGe-on-insulator virtual substrate with a high Ge fraction", Applied Physics Letters, 79, pp. 1798-1800 (2001).
↓	F. Y. Huang et al., "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate", Applied Physics Letters, 76, pp. 2680-2682 (2000).

Examiner	<i>Victor A. Mandala Jr.</i>	Date Considered	<i>5-24-05</i>
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